

<p>INFORMATION DISCLOSURE STATEMENT BY APPLICANTS PTO FORM 1449</p>	<p>Atty. Docket No. 10191/4133</p>	<p>Serial No. 10/529425 To Be Assigned</p>
	<p>Applicant(s) LAMMEL et al.</p>	
	<p>Filing Date Herewith</p>	<p>Group To Be Assigned 1763</p>

U. S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NUMBER	PATENT DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>gag</i>	5,542,558*	Aug. 6, 1996	OFFENBERG et al.			
<i>gag</i>	5,594,171*	Jan. 14, 1997	IMAEDA et al.			

* Copy of reference is not enclosed because reference is cited in Search Report (copy of reference provided by International Searching Authority).

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
<i>gag</i>	02 051741*	Jul. 4, 2002	PCT			YES NO
<i>gag</i>	1 088 785*	Apr. 4, 2001	Europe			
<i>gag</i>	0 895 276*	Feb. 3, 1999	Europe			

* Copy of reference is not enclosed because reference is cited in Search Report (copy of reference provided by International Searching Authority).

OTHER DOCUMENTS

EXAMINER'S INITIALS	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
<i>gag</i>	Lee et al., <i>A New Wide-Dimensional Freestanding Microstructure Fabrication Technology Using Laterally Formed Porous Silicon as a Sacrificial Layer</i> , Sensors and Actuators, Lausanne, Switzerland, Vol. 84, No. 1-2, Aug. 1, 2000, pgs. 181-5.*
<i>gag</i>	Splinter et al., <i>Thick Porous Silicon Formation Using Implanted Mask Technology</i> , Sensors and Actuators, Lausanne, Switzerland, Vol. 76, No. 1-3, pgs. June 1, 2001, 354-60.*

* Copy of reference is not enclosed because reference is cited in Search Report (copy of reference provided by International Searching Authority).

<p>EXAMINER <i>George A Goudreau</i></p>	<p>DATE CONSIDERED 12-06'</p>
<p>EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

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